

**Silicon NPN Power Transistors**

**BUW35**

**DESCRIPTION**

- With TO-3 package
- High breakdown voltage

**APPLICATIONS**

- For high voltage ,fast switching applications

**PINNING (See Fig.2)**

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

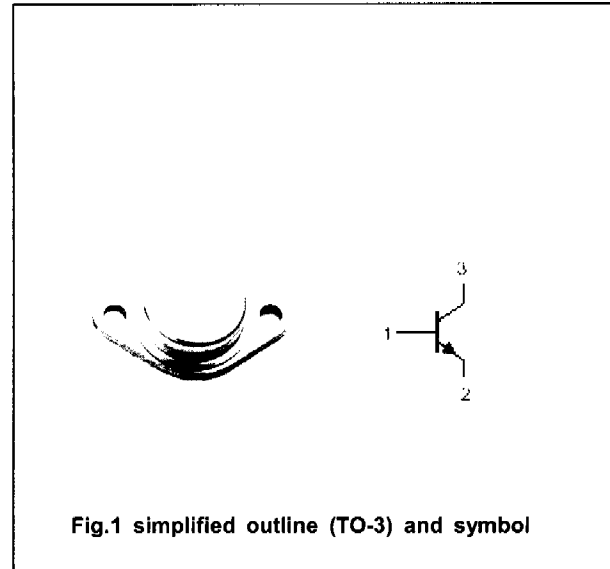


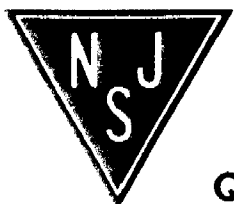
Fig.1 simplified outline (TO-3) and symbol

**Absolute maximum ratings(Ta=25 )**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CB0</sub>	Collector-base voltage	Open emitter	800	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	400	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	7	V
I <sub>C</sub>	Collector current		10	A
I <sub>CM</sub>	Collector current-peak		15	A
I <sub>B</sub>	Base current		5	A
P <sub>T</sub>	Total power dissipation	T <sub>C</sub> ≤25	125	W
T <sub>J</sub>	Junction temperature		200	
T <sub>stg</sub>	Storage temperature		-65-200	

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	VALUE	UNIT
R <sub>th-j-c</sub>	Thermal resistance from junction to case	1.4	/W



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# BUW35

## CHARACTERISTICS

T<sub>j</sub>=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-emitter sustaining voltage	I <sub>C</sub> =100mA; I <sub>B</sub> =0	400			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =8A; I <sub>B</sub> =2.5A			1.5	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =8A; I <sub>B</sub> =2.5A			1.8	V
I <sub>CES</sub>	Collector cut-off current	V <sub>CE</sub> =800V; V <sub>BE</sub> =0 T <sub>C</sub> =125			0.1 3.0	mA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =7V; I <sub>C</sub> =0			1	mA
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =1A; V <sub>CE</sub> =5V	15		50	
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =5A; V <sub>CE</sub> =5V	8			

### Switching times

t <sub>on</sub>	Turn-on time	I <sub>C</sub> =5A; I <sub>B1</sub> =- I <sub>B2</sub> =1A V <sub>CC</sub> =250V			0.7	μs
t <sub>s</sub>	Storage time				3.0	μs
t <sub>f</sub>	Fall time				0.8	μs

PACKAGE OUTLINE

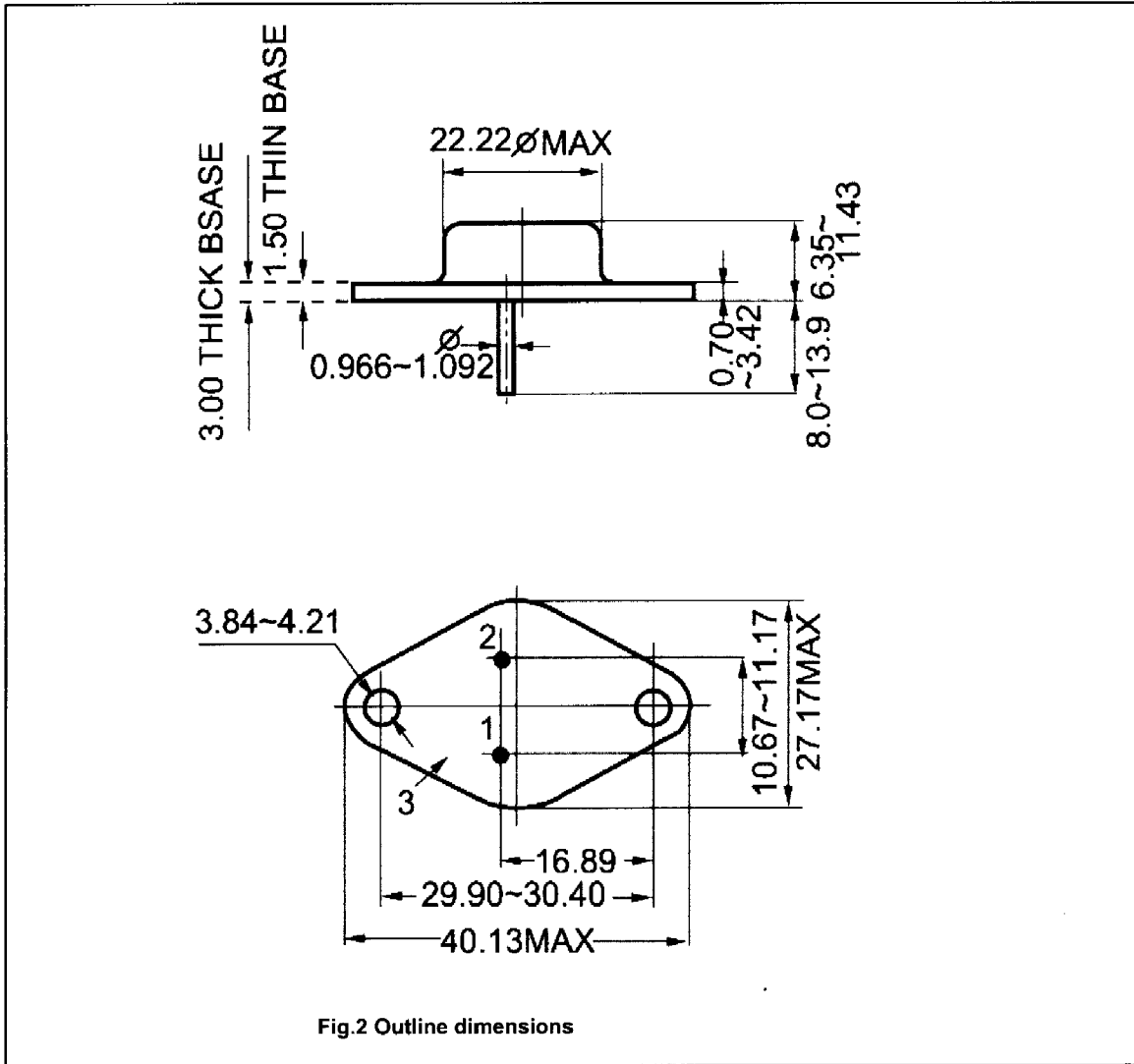


Fig.2 Outline dimensions